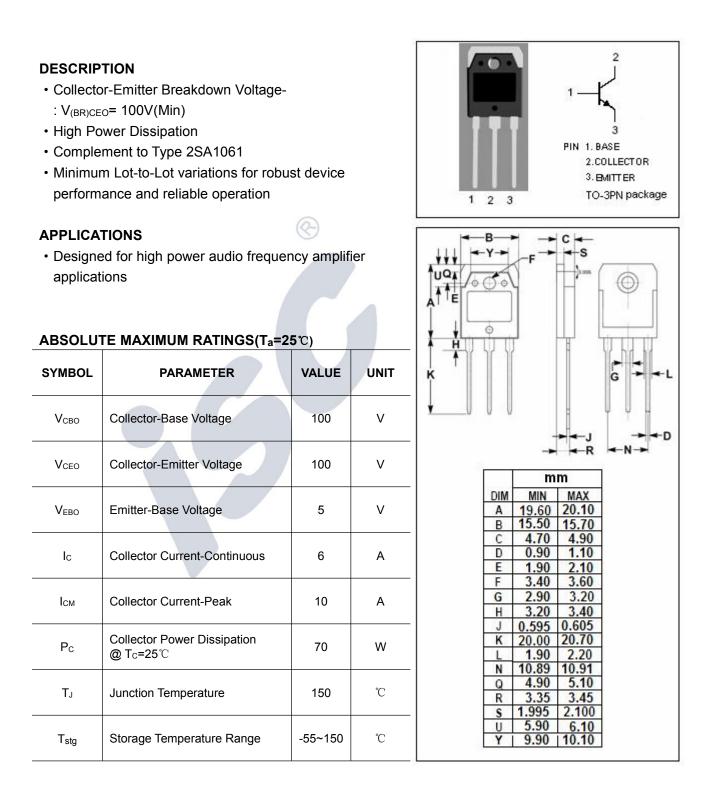


isc Silicon NPN Power Transistor

2SC2485





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ELECTRICAL CHARACTERISTICS

$T_c \text{=} 25^{\circ}\!\!\!\! \mathbb{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 30mA; I _B = 0	100			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 4A; I _B = 0.4A			2.0	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = 4A; V _{CE} = 5V			1.8	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 100V; I _E = 0			50	μA
І _{ЕВО}	Emitter Cutoff Current	V _{EB} = 3V; I _C = 0			50	μA
h _{FE-1}	DC Current Gain	I _C = 0.2A; V _{CE} = 5V	20			
h _{FE-2}	DC Current Gain	I _C = 1A; V _{CE} = 5V	40		200	
h _{FE-3}	DC Current Gain	Ic= 4A; Vc= 5V	20			
fT	Current-Gain—Bandwidth Product	I _C = 0.5A; V _{CE} = 5V		20		MHz

h_{FE-2} Classifications

R	Q	Р
40-80	60-120	100-200

Notice:

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